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Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	ARM9®
Core Size	16/32-Bit
Speed	96MHz
Connectivity	CANbus, I ² C, IrDA, Microwire, SPI, SSI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	40
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 2V
Data Converters	A/D 8x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str910fam32x6

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Description STR91xFAxxx

1 Description

STR91xFA is a series of ARM®-powered microcontrollers which combines a 16/32-bit ARM966E-S RISC processor core, dual-bank Flash memory, large SRAM for data or code, and a rich peripheral set to form an ideal embedded controller for a wide variety of applications such as point-of-sale terminals, industrial automation, security and surveillance, vending machines, communication gateways, serial protocol conversion, and medical equipment. The ARM966E-S core can perform single-cycle DSP instructions, good for speech processing, audio algorithms, and low-end imaging.



Functional overview STR91xFAxxx

3 Functional overview

3.1 System-in-a-package (SiP)

The STR91xFA is a SiP device, comprised of two stacked die. One die is the ARM966E-S CPU with peripheral interfaces and analog functions, and the other die is the burst Flash. The two die are connected to each other by a custom high-speed 32-bit burst memory interface and a serial JTAG test/programming interface.

3.2 Package choice

STR91xFA devices are available in 128-pin (14 x 14 mm) and 80-pin (12 x 12 mm) LQFP and LFBGA144 (10 x 10 mm) packages. Refer to *Table 2: Device summary on page 11* for a list of available peripherals for each of the package choices.

3.3 ARM966E-S CPU core

The ARM966E-S core inherently has separate instruction and data memory interfaces (Harvard architecture), allowing the CPU to simultaneously fetch an instruction, and read or write a data item through two Tightly-Coupled Memory (TCM) interfaces as shown in *Figure 1*. The result is streamlined CPU Load and Store operations and a significant reduction in cycle count per instruction. In addition to this, a 5-stage pipeline is used to increase the amount of operational parallelism, giving the most performance out of each clock cycle.

Ten DSP-enhanced instruction extensions are supported by this core, including single-cycle execution of 32x16 Multiply-Accumulate, saturating addition/subtraction, and count leading-zeros.

The ARM966E-S core is binary compatible with 32-bit ARM7 code and 16-bit Thumb® code.

3.4 Burst Flash memory interface

A burst Flash memory interface (*Figure 1*) has been integrated into the Instruction TCM (I-TCM) path of the ARM966E-S core. Also in this path is an 8-instruction Pre-Fetch Queue (PFQ) and a 15-entry Branch Cache (BC), enabling the ARM966E-S core to perform up to 96 MIPS while executing code directly from Flash memory. This architecture provides high performance levels without a costly instruction SRAM, instruction cache, or external SDRAM. Eliminating the instruction cache also means interrupt latency is reduced and code execution becomes more deterministic.

3.4.1 Pre-fetch queue (PFQ)

As the CPU core accesses sequential instructions through the I-TCM, the PFQ always looks ahead and will pre-fetch instructions, taking advantage any idle bus cycles due to variable length instructions. The PFQ will fetch 32-bits at a time from the burst Flash memory at a rate of up to 96 MHz.

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3.5 SRAM (64 Kbytes or 96 Kbytes)

A 32-bit wide SRAM resides on the CPU's Data TCM (D-TCM) interface, providing single-cycle data accesses. As shown in *Figure 1*, the D-TCM shares SRAM access with the Advanced High-performance Bus (AHB). Sharing is controlled by simple arbitration logic to allow the DMA unit on the AHB to also access the SRAM.

3.5.1 Arbitration

Zero-wait state access occurs for either the D-TCM or the AHB when only one of the two is requesting SRAM. When both request SRAM simultaneously, access is granted on an interleaved basis so neither requestor is starved, granting one 32-bit word transfer to each requestor before relinquishing SRAM to the other. When neither the D-TCM or the AHB are requesting SRAM, the arbiter leaves access granted to the most recent user (if D-TCM was last to use SRAM then the D-TCM will not have to arbitrate to get access next time).

The CPU may execute code from SRAM through the AHB. There are no wait states as long as the D-TCM is not contending for SRAM access and the AHB is not sharing bandwidth with peripheral traffic. The ARM966E-S CPU core has a small pre-fetch queue built into this instruction path through the AHB to look ahead and fetch instructions during idle bus cycles.

3.5.2 Battery backup

When a battery is connected to the designated battery backup pin (VBATT), SRAM contents are automatically preserved when the operating voltage on the main digital supplies (VDD and VDDQ are lost or sag below the LVD threshold. Automatic switchover to SRAM can be disabled by firmware if it is desired that the battery will power only the RTC and not the SRAM during standby.

3.6 DMA data movement

DMA channels on the Advanced High-performance Bus (AHB) take full advantage of the separate data path provided by the Harvard architecture, moving data rapidly and largely independent of the instruction path. There are two DMA units, one is dedicated to move data between the Ethernet interface and SRAM, the other DMA unit has eight programmable channels with 14 request signals to service other peripherals and interfaces (USB, SSP, ADC, UART, Timers, EMI, and external request pins). Both single word and burst DMA transfers are supported. Memory-to-memory transfers are supported in addition to memory-peripheral transfers. DMA access to SRAM is shared with D-TCM accesses, and arbitration is described in *Section 3.5.1*. Efficient DMA transfers are managed by firmware using linked list descriptor tables. Of the 16 DMA request signals, two are assigned to external inputs. The DMA unit can move data between external devices and resources inside the STR91xFA through the EMI bus.



STR91xFAxxx Functional overview

3.12.2 Battery supply

An optional stand-by voltage from a battery or other source may be connected to pin VBATT to retain the contents of SRAM in the event of a loss of the main digital supplies (V_{DD} and V_{DDQ}). The SRAM will automatically switch its supply from the internal V_{DD} source to the VBATT pin when the voltage of V_{DD} drops below the LVD threshold. In order to use the battery supply, the LVD must be enabled.

The VBATT pin also supplies power to the RTC unit, allowing the RTC to function even when the main digital supplies (V_{DD} and V_{DDQ}) are switched off. By configuring the RTC register, it is possible to select whether or not to power from VBATT only the RTC unit, or power the RTC unit and the SRAM when the STR91xFA device is powered off.

3.13 System supervisor

The STR91xFA monitors several system and environmental inputs and will generate a global reset, a system reset, or an interrupt based on the nature of the input and configurable settings. A global reset clears all functions on the STR91xFA, a system reset will clear all but the Clock Control Unit (CCU) settings and the system status register. At any time, firmware may reset individual on-chip peripherals. System supervisor inputs include:

- GR: CPU voltage supply (V_{DD}) drop out or brown out
- GR: I/O voltage supply (V_{DDO}) drop out or brown out
- GR: Power-Up condition
- SR: Watchdog timer timeout
- SR: External reset pin (RESET_INn)
- SR: JTAG debug reset command

Note: GR: means the input causes Global Reset, SR: means the input causes System Reset

The CPU may read a status register after a reset event to determine if the reset was caused by a watchdog timer timeout or a voltage supply drop out. This status register is cleared only by a power up reset.

3.13.1 Supply voltage brownout

Each operating voltage source (V_{DD} and V_{DDQ}) is monitored separately by the Low Voltage Detect (LVD) circuitry. The LVD will generate an early warning interrupt to the CPU when voltage sags on either V_{DD} or V_{DDQ} voltage inputs. This is an advantage for battery powered applications because the system can perform an orderly shutdown before the batteries become too weak. The voltage trip point to cause a brown out interrupt is typically 0.25V above the LVD dropout thresholds that cause a reset.

CPU firmware may prevent all brown-out interrupts by writing to interrupt mask registers at run-time.

Functional overview STR91xFAxxx

3.18.1 Packet buffer interface (PBI)

The PBI manages a set of buffers inside the 2 Kbyte Packet Buffer, both for transmission and reception. The PBI will choose the proper buffer according to requests coming from the USB Serial Interface Engine (SIE) and locate it in the Packet SRAM according to addresses pointed by endpoint registers. The PBI will also auto-increment the address after each exchanged byte until the end of packet, keeping track of the number of exchanged bytes and preventing buffer overrun. Special support is provided by the PBI for isochronous and bulk transfers, implementing double-buffer usage which ensures there is always an available buffer for a USB packet while the CPU uses a different buffer.

3.18.2 DMA

A programmable DMA channel may be assigned by CPU firmware to service the USB interface for fast and direct transfers between the USB bus and SRAM with little CPU involvement. This DMA channel includes the following features:

- Direct USB Packet Buffer SRAM to system SRAM transfers of receive packets, by descriptor chain for bulk or isochronous endpoints.
- Direct system SRAM to USB Packet Buffer SRAM transfers of transmit packets, by descriptor chain for bulk or isochronous endpoints.
- Linked-list descriptor chain support for multiple USB packets

3.18.3 Suspend mode

CPU firmware may place the USB interface in a low-power suspend mode when required, and the USB interface will automatically wake up asynchronously upon detecting activity on the USB pins.

3.19 CAN 2.0B interface

The STR91xFA provides a CAN interface complying with CAN protocol version 2.0 parts A and B. An external CAN transceiver device connected to pins CAN_RX and CAN_TX is required for connection to the physical CAN bus.

The CAN interface manages up to 32 Message Objects and Identifier Masks using a Message SRAM and a Message Handler. The Message Handler takes care of low-level CAN bus activity such as acceptance filtering, transfer of messages between the CAN bus and the Message SRAM, handling of transmission requests, and interrupt generation. The CPU has access to the Message SRAM via the Message Handler using a set of 38 control registers.

The follow features are supported by the CAN interface:

- Bit rates up to 1 Mbps
- Disable Automatic Retransmission mode for Time Triggered CAN applications
- 32 Message Objects
- Each Message Object has its own Identifier Mask
- Programmable FIFO mode
- Programmable loopback mode for self-test operation

The CAN interface is not supported by DMA.



STR91xFAxxx Functional overview

3.26 Three-phase induction motor controller (IMC)

The STR91xFA provides an integrated controller for variable speed motor control applications.

Six PWM outputs are generated on high current drive pins P6.0 to P6.5 for controlling a three-phase AC induction motor drive circuit assembly. Rotor speed feedback is provided by capturing a tachometer input signal on pin P6.6, and an asynchronous hardware emergency stop input is available on pin P6.7 to stop the motor immediately if needed, independently of firmware.

The IMC unit has the following features:

- Three PWM outputs generated using a 10 or 16-bit PWM counter, one for each phase U, V, W. Complimentary PWM outputs are also generated for each phase.
- Choice of classic or zero-centered PWM generation modes
- 10 or 16-bit PWM counter clock is supplied through a programmable 8-bit prescaler of the APB clock.
- Programmable 6 or 10-bit dead-time generator to add delay to each of the three complimentary PWM outputs
- 8-bit repetition counter
- Automatic rotor speed measurement with 16-bit resolution. Schmitt trigger tachometer input with programmable edge detection
- Hardware asynchronous emergency stop input
- A dedicated interrupt to CPU with eight flags
- Enhanced Motor stop output polarity configuration
- Double update option when PWM counter reaches the max and min values in Zerocentered mode
- Locking feature to prevent some control register bits from being advertently modified
- Trigger output to start an ADC conversion



Functional overview STR91xFAxxx

3.27 External memory interface (EMI)

STR91xFA devices in 128-pin and 144-ball packages offer an external memory bus for connecting external parallel peripherals and memories. The EMI bus resides on ports 7, 8, and 9 and operates with either an 8 or 16-bit data path. The configuration of 8 or 16 bit mode is specified by CPU firmware writing to configuration registers at run-time. If the application does not use the EMI bus, then these port pins may be used for general purpose I/O as shown in *Table 8*.

The EMI has the following features:

- Supports static asynchronous memory access cycles, including page mode for nonmux operation. The bus control signals include:
 - EMI RDn read signal, x8 or x16 mode
 - EMI_BWR_WRLn write signal in x8 mode and write low byte signal in x16 mode
 - EMI WRHn write high byte signal in x16 mode
 - EMI_ALE address latch signal for x8 or x16 mux bus mode with programmable polarity
- Four configurable memory regions, each with a chip select output (EMI_CS0n ... EMI_CS3n)
- Programmable wait states per memory region for both write and read operations
- 16-bit multiplexed data mode (Figure 4): 16 bits of data and 16 bits of low-order address are multiplexed together on ports 8 and 9, while port 7 contains eight more high-order address signals. The output signal on pin EMI_ALE is used to demultiplex the signals on ports 8 and 9, and the polarity of EMI_ALE is programmable. The output signals on pins EMI_BWR_WRLn and EMI_WRHn are the write strobes for the low and high data bytes respectively. The output signal EMI_RDn is the read strobe for both the low and high data bytes.
- **8-bit multiplexed data mode**: This is a variant of the 16-bit multiplexed mode. Although this mode can provide 24 bits of address and 8 bits of data, it does require an external latch device on Port 8. However, this mode is most efficient when connecting devices that only require 8 bits of address on an 8-bit multiplexed address/data bus, and have simple read, write, and latch inputs as shown in *Figure 5*

To use all 24 address bits, the following applies: 8 bits of lowest-order data and 8 bits of lowest-order address are multiplexed on port 8. On port 9, 8-bits of mid-order address are multiplexed with 8 bits of data, but these 8 data values are always at logic zero on this port during a write operation, and these 8 data bits are ignored during a read operation. An external latch device is needed to de-multiplex the mid-order 8 address bits that are generated on port 8. Port 7 outputs the 8 highest-order address signals directly (not multiplexed). The output signal on pin EMI_ALE is used to demultiplex the signals on ports 8 and 9, and the polarity of EMI_ALE is programmable. The output signal on pin



STR91xFAxxx Pin description

Table 8. Device pin description (continued)

Package			Ф		-		Alternate	functions			
LQFP80	LQFP128	LFBGA144	Pin name	Signal type	Default pin function	Default input function	Alternate input 1	Alternate output 1	Alternate output 2	Alternate output 3	
-	21	G4	EMI_ BWR_ WRLn	0	EMI byte write strobe (8 bit mode) or low byte write strobe (16 bit mode) Can also be configured as EMI_LBn in BGA package			N/A			
-	22	H1	EMI_ WRHn	0	EMI high byte write strobe (16-bit mode) Can also be configured as EMI_UBn in BGA package		N/A				
-	74	J10	EMI_ALE	0	EMI address latch enable (mux mode)			N/A			
-	75	J9	EMI_ RDn	0	EMI read strobe			N/A			
-	-	Н8	EMI_ BAAn	0	EMI Burst address advance			N/A			
-	-	K8	EMI_ WAITn	I	EMI Wait input for burst mode device			N/A			
-	-	M8	EMI_ BCLK	0	EMI bus clock			N/A			
-	-	A12	EMI_ WEn	0	EMI write enable			N/A			
-	91	E10	TAMPER _IN	1	Tamper detection input			N/A			
-	94	D11	MII_ MDIO	I/O	MAC/PHY management data line			N/A			
59	95	D10	USBDN	I/O	USB data (-) bus connect			N/A			
60	96	C11	USBDP	I/O	USB data (+) bus connect		N/A				
56	89	C12	RESET _INn	_	External reset input		N/A				
62	100	A9	RESET _OUTn	0	Global or System reset output	N/A					
65	104	A10	X1_CPU	I	CPU oscillator or crystal input	N/A					
64	103	A11	X2_CPU	0	CPU crystal connection			N/A			

Electrical characteristics STR91xFAxxx

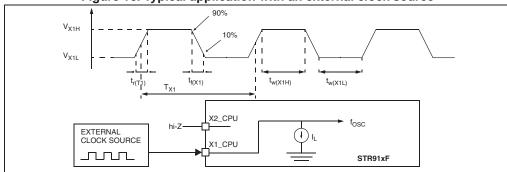


Figure 16. Typical application with an external clock source

7.7.3 RTC clock generated from a crystal/ceramic resonator

The RTC (Real-Time Clock) can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph is based on characterization results obtained with typical external components specified in *Table 20 & Table 21*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Note:

For CL1 and CL2 it is recommended to use high-quality ceramic capacitors in the 5 pF to 16 pF range, selected to match the requirements of the crystal or resonator. CL1 and CL2, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of CL1 and CL2.

Load capacitance CL has the following formula:

 $CL = CL1 \times CL2 / (CL1 + CL2) + Cstray$

where Cstray is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution:

Never use a resonator with a load capacitance of 12.5 pF.

Example: if you choose a resonator with a load capacitance of CL = 6 pF, and Cstray = 2 pF, then CL1 = CL2 = 8 pF.

Conditions: V_{DDO} = 2.7 - 3.6 V, V_{DD} = 1.65 - 2 V, T_A = -40 / 85 °C unless otherwise specified.

Symbol	Parameter	Test	Va	Unit		
Symbol	raiailletei	conditions	Min	Тур	Max	Oilit
R _F	External feedback resistor			22		ΜΩ
V _{START(RTC)}	Oscillator start voltage		V _{DD_LVD+} (1)			V
9 _M	Oscillator transconductance ⁽²⁾	Start-up	1.8			μΑ/Volts
t _{STUP(RTC)}	Oscillator Start-up Time ⁽²⁾	V _{DD} stable			1	S

Table 20. RTC oscillator electrical characteristics



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^{1.} Refer to Table 14 for min. value of V_{DD_LVD+}

^{2.} Data based on bench measurements, not tested in production.

7.10 I/O characteristics

 V_{DDQ} = 2.7 - 3.6 V, V_{DD} = 1.65 - 2 V, T_{A} = -40 / 85 °C unless otherwise specified.

Table 31. I/O characteristics

Symbol	Parameter	Test conditions		Value				
Symbol	Farameter	rest conditions	Min	Тур	Тур Мах			
		General inputs ⁽¹⁾	2.0		(2)	V		
		RESET and TCK inputs ⁽¹⁾	0.8 V _{DDQ}					
V_{IH}	Input high level	TAMPER_IN input ⁽³⁾ (Run mode)	V _{DDQ} /2					
		TAMPER_IN input ⁽³⁾ (Standby mode)	V _{BAT} /2					
		General inputs ⁽¹⁾			0.8			
		RESET and TCK inputs ⁽¹⁾			0.2 V _{DDQ}			
V_{IL}	Input low level	TAMPER_IN input ⁽³⁾ (Run mode)			V _{DDQ} /2			
		TAMPER_IN input ⁽³⁾ (Standby mode)			V _{BAT} /2			
V _{HYS}	Input hysteresis Schmitt trigger	General inputs ⁽⁴⁾			0	V		
	Output high level High current pins	I/O ports 3 and 6: Push-Pull, I _{OH} = 8mA	V _{DDQ} -0.7					
V_{OH}	Output high level Standard current pins	I/O ports 0,1,2,4,5,7,8,9: Push-Pull, I _{OH} = 4mA	V _{DDQ} -0.7			V		
V _{OH}	Output high level JTAG JTDO pin	I _{OH} = -100 μA	V _{DDQ} -0.1					
	Output low level High current pins	I/O ports 3 and 6: Push-Pull, I _{OL} = 8mA			0.4			
V_{OL}	Output low level Standard current pins	I/O ports 0,1,2,4,5,7,8,9: Push-Pull, I _{OL} = 4mA			0.4	V		
	Output low level JTAG JTDO pin	I _{OL} =100 μA			0.1			

^{1.} Guaranteed by characterization, not tested in production.

^{2.} Input pins are 5V tolerant, max input voltage is 5.5V

^{3.} Guaranteed by design, not tested in production.

^{4.} TAMPER_IN pin and STR9 general inputs have no built-in hysteresis.

Mux read

EMI_ALE

EMI_A[23:16]

Address

EMI_AD[15:0]

Address

Data

t_ROB

TROB

Figure 21. Mux read diagram

Table 36. Mux read times

Symbol	Parameter	Value					
Syllibol	Farameter	Min	Max				
t _{RCR}	Read to CSn inactive	0	1.5 ns				
t _{RAS}	Read address setup time	((WSTOEN) x t _{BCLK})- 4 ns	((WSTOEN) x t _{BCLK})				
t _{RDS}	Read data setup time	12 ns	-				
t _{RDH}	Read data hold time	0					
t _{RP}	Read pulse width	((WSTRD-WSTOEN+1) x t _{BCLK}) - 0.5 ns	((WSTRD-WSTOEN+1) x t _{BCLK}) + 2.5 ns				
t _{AW}	ALE pulse width	(ALE_LENGTH x t _{BCLK}) - 3.5 ns	(ALE_LENGTH x t _{BCLK})				
t _{AAS}	Address to ALE setup time	(ALE_LENGTH x t _{BCLK}) - 3.5 ns	(ALE_LENGTH x t _{BCLK})				
t _{AAH}	Address to ALE hold time	(t _{BCLK} /2)- 1 ns	(t _{BCLK} /2) + 2 ns				

Electrical characteristics STR91xFAxxx

7.12 Communication interface electrical characteristics

7.12.1 10/100 Ethernet MAC electrical characteristics

 V_{DDQ} = 2.7 - 3.6 V, V_{DD} = 1.65 - 2 V, T_A = -40 / 85 °C unless otherwise specified.

Ethernet MII interface timings

Figure 25. MII_RX_CLK and MII_TX_CLK timing diagram

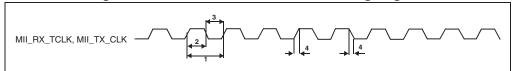


Table 40. MII_RX_CLK and MII_TX_CLK timing table

Symbol	Parameter	Symbol	Va	Unit	
Symbol	Farameter	Symbol	Min	Max	Offic
1	Cycle time	t _c (CLK)	40		ns
2	Pulse duration high	t _{HIGH} (CLK)	40%	60%	
3	Pulse duration low	t _{LOW} (CLK)	40%	60%	
4	Transition time	t _t (CLK)		1	ns

Figure 26. MDC timing diagram

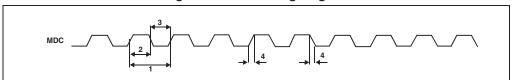


Table 41. MDC timing table

Symbol	Parameter	Symbol	Va	Unit		
Symbol	Farameter	Syllibol	Min	Max	Onit	
1	Cycle time	t _c (MDC)	266		ns	
2	Pulse duration high	t _{HIGH} (MDC)	40%	60%		
3	Pulse duration low	t _{LOW} (MDC)	40%	60%		
4	Transition time	t _t (MDC)		1	ns	

Ethernet MII management timings

Figure 27. Ethernet MII management timing diagram

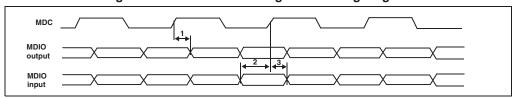
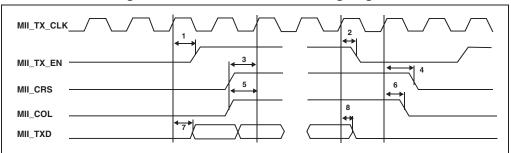


Table 42. Ethernet MII management timing table

Symbol	Parameter	Symbol	Va	Unit	
Symbol	raiailletei	Symbol	Min	Max	Oille
1	MDIO delay from rising edge of MDC	t _c (MDIO)		2.83	ns
2	MDIO setup time to rising edge of MDC	T _{su} (MDIO)	2.70		ns
3	MDIO hold time from rising edge of MDC	T _h (MDIO)	-2.03		ns

Ethernet MII transmit timings

Figure 28. Ethernet MII transmit timing diagram



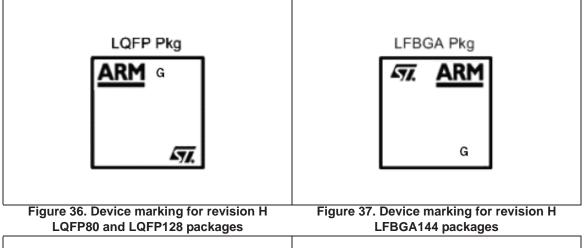
STR91xFAxxx Device marking

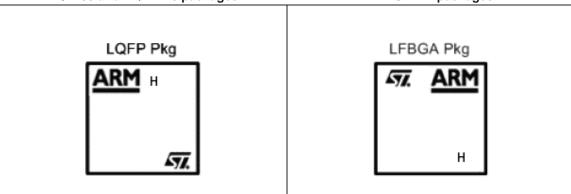
8 Device marking

8.1 STR91xFAx32 / STR91xFAx42 / STR91xFAx44

Figure 34. Device marking for revision G
LQFP80 and LQFP128 packages

Figure 35. Device marking for revision G
LFBGA144 packages





Device marking STR91xFAxxx

8.2 STR91xFAx46 / STR91xFAx47

Figure 38. Device marking for revision A LQFP80 and LQFP128 packages

Figure 39. Device marking for revision A LFBGA144 packages

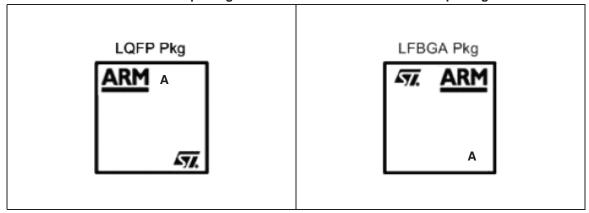


Table 52.LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package mechanical data

Symbol		millimeters		inches ⁽¹⁾			
Symbol	Min	Тур	Max	Тур	Min	Max	
A ⁽²⁾	-	-	1.700			0.0669	
A1	0.210	-	-	0.0083			
A2	-	1.060	-		0.0417		
A3		0.026			0.0010		
A4	-	0.800	-	-	0.0315	-	
b	0.350	0.400	0.450	0.0138	0.0157	0.0177	
D	9.850	10.000	10.150	0.3878	0.3937	0.3996	
D1	-	8.800	-	-	0.3465	-	
Е	9.850	10.000	10.150	0.3878	0.3937	0.3996	
E1	-	8.800	-	-	0.3465	-	
е	-	0.800	-	-	0.0315	-	
F	-	0.600	-	-	0.0236	-	
ddd		0.100		0.0039			
eee		0.150			0.0059		
fff		0.080			0.0031		

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.



^{2.} STATSChipPAC package dimensions.

Revision history STR91xFAxxx

11 Revision history

Table 55. Document revision history

Date	Revision	Changes
09-May-2007	1	Initial release
26-Nov-2007	2	Updated Standby current in <i>Table 15: Supply current</i> characteristics on page 64 Added Section 7.1: Parameter conditions on page 58 Added Section 7.7.2: X1_CPU external clock source on page 67 Updated Section 7.11: External memory bus timings on page 76 Added Figure 14: LVD reset delay case 3 on page 63 Added <i>Table 48</i> and <i>Table 49</i> in ADC characteristics section Added min/max values for E, D, E1, D1 in <i>Figure 43</i> on page 98
14-May-2008	3	Added 1MB and 2M devices, creating merged datasheet from seperate STR91xFAx32, 42, 44, 46 and 47 devices. Added STR912FAW32 to Table 1: Device summary on page 1 Added paragraph on voltage supply shutdown in Section 3.12 on page 24 Removed DMA feature for I2C in Section 3.21 on page 33 Updated Sleep mode current in Table 10: Current characteristics on page 60 Added Table 16: Typical current consumption at 25 °C on page 65 Updated operating conditions for V _{DD} and f _{CPUCLK} in Section 7.3 on page 61 and Section 7.7: Clock and timing characteristics on page 66 Changed SPI master t _{SU} and t _{H to} TBD in Table 46: SPI electrical characteristics on page 88
17-Jul-2008	4	Updated Section 3.10.6: UART and SSP clock (BRCLK) on page 22 Updated Table 11: Operating conditions on page 61 Updated I _{SLEEP(IDDQ)} in Table 15: Supply current characteristics on page 64 Updated Table 17: Internal clock frequencies on page 66 Updated Table 31: I/O characteristics on page 75
22-Dec-2008	5	Updated Section 7.7.3 on page 68. Small text changes.

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